

10/031117

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Page 1 of 1

FORM PTO-1449			Atty. Docket No.	Appln. No.
<u>LIST OF DOCUMENTS CITED BY APPLICANT</u>			XA-9593	10/031117
			Applicant	Takashi KOBAYASHI et al.
			Filing Date	Group
			HEREWITH	282~

U.S. PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Name	Class	Sub-class	Filing Date
MT	AA	5,780,341	7/14/98	Ogura	438	259	
	AB	5,654,917	8/5/97	Ogura et al.	365	185	
	AC	5,541,130	7/30/96	Ogura et al.	437	43	
	AD	5,672,892	9/30/97	Ogura et al.	257	314	
MT	AE	5,681,770	10/28/97	Ogura et al.	437	43	
	AF						
	AG						
	AH						
	AI						

FOREIGN PATENT DOCUMENTS

Examiner Initial		Document Number	Date	Country	Class	Sub-class	Translation
MT	AL	11-220044	8/10/99	Japan ✓	—	—	abstract
	AM	63-25979	2/3/88	Japan ✓	—	—	abstract
	AN	9-116119	5/2/97	Japan ✓	—	—	abstract
	AO	7-130884	5/19/95	Japan	—	—	abstract
	AP	8-340095	12/24/96	Japan	—	—	abstract
MT	AQ	9-321157	12/12/97	Japan	—	—	abstract

OTHER (including author, title, date, pertinent pages, etc.)

MT	AR	Kume, Hitoshi, "Flash Memory Technology," Ohyobutsuri, 65, No. 11, pp. 1114-1124, November 10, 1996 (Japan Society of Applied Physics)
MT	AS	Naruke, K. et al., "A New Flash-Erase EEPROM Cell with a Sidewall Select-Gate on its Source Side", IEEE Technical Digest of International Electron Devices Meeting, 1989, pp. 603-606.

Examiner	Michael Trich	Date Considered
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.